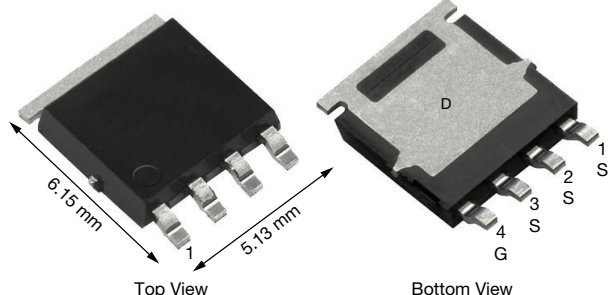


# N-Channel 40 V (D-S) MOSFET

PowerPAK® SO-8L Single



## FEATURES

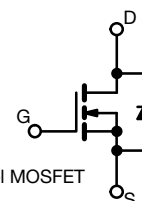
- TrenchFET® Gen IV power MOSFET
- Very low  $Q_g$  and  $Q_{oss}$  reduce power loss and improve efficiency
- Flexible leads provide resilience to mechanical stress
- 100 %  $R_g$  and UIS tested
- $Q_{gd}/Q_{gs}$  ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- Synchronous rectification
- High power density DC/DC
- DC/AC inverters



N-Channel MOSFET

## PRODUCT SUMMARY

$V_{DS}$ (V)	40
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.00475
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.0067
$Q_g$ typ. (nC)	10.9
$I_D$ (A) <sup>a</sup>	78
Configuration	Single

## ORDERING INFORMATION

Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SiJ4406DP-T1-GE3

## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	40	V
Gate-source voltage	$V_{GS}$	+20, -16	
Continuous drain current ( $T_J = 150$ °C)	$T_C = 25$ °C	78	A
	$T_C = 70$ °C	62.4	
	$T_A = 25$ °C	21.3 <sup>b, c</sup>	
	$T_A = 70$ °C	17 <sup>b, c</sup>	
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{DM}$	200	
Continuous source-drain diode current	$T_C = 25$ °C	47.3	
	$T_A = 25$ °C	3.5 <sup>b, c</sup>	
Single pulse avalanche current	$L = 0.1$ mH	20	
Single pulse avalanche energy	$E_{AS}$	20	mJ
Maximum power dissipation	$T_C = 25$ °C	41.6	W
	$T_C = 70$ °C	26.6	
	$T_A = 25$ °C	3.9 <sup>b, c</sup>	
	$T_A = 70$ °C	2.5 <sup>b, c</sup>	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>d, e</sup>		260	

## THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction to ambient <sup>b, f</sup>	$R_{thJA}$	23	32	°C/W
Maximum junction to case (drain)	$R_{thJC}$	2.4	30	

### Notes

- $T_C = 25$  °C
- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 70 °C/W



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	40	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 1 mA	-	29	-	mV/°C
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	-4.5	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.1	-	2.4	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = +20, -16 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 75 °C	-	-	20	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	-	0.00385	0.00475	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	0.0053	0.0067	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 15 A	-	60	-	S
Dynamic <sup>b</sup>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	1851	-	pF
Output capacitance	C <sub>oss</sub>		-	326	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	26	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	-	23.7	35.5	nC
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	10.9	16.5	
Q <sub>gs</sub>	-		5.3	-		
Q <sub>gd</sub>	-		1.9	-		
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V	-	12	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz	1.4	2.8	4.7	Ω
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20 V, R <sub>L</sub> = 2 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	11	22	ns
Rise time	t <sub>r</sub>		-	5	10	
Turn-off delay time	t <sub>d(off)</sub>		-	22	44	
Fall time	t <sub>f</sub>		-	6	12	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20 V, R <sub>L</sub> = 2 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	19	38	
Rise time	t <sub>r</sub>		-	50	100	
Turn-off delay time	t <sub>d(off)</sub>		-	22	44	
Fall time	t <sub>f</sub>		-	9	18	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	47.3	A
Pulse diode forward current (t <sub>p</sub> = 100 μs)	I <sub>SM</sub>		-	-	200	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = 5 A	-	0.75	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	22	44	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	9	18	nC
Reverse recovery fall time	t <sub>a</sub>		-	11	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	11	-	

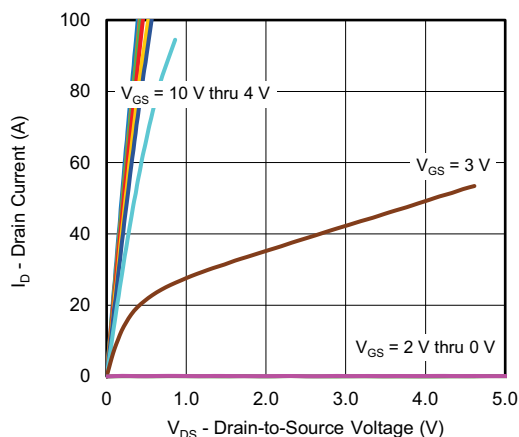
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

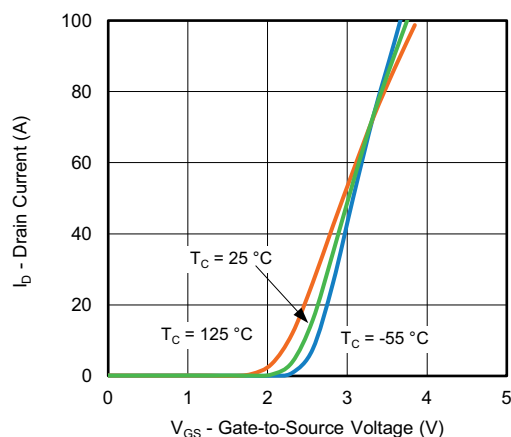
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



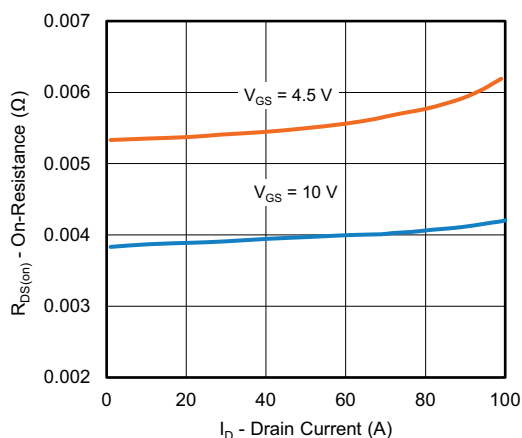
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



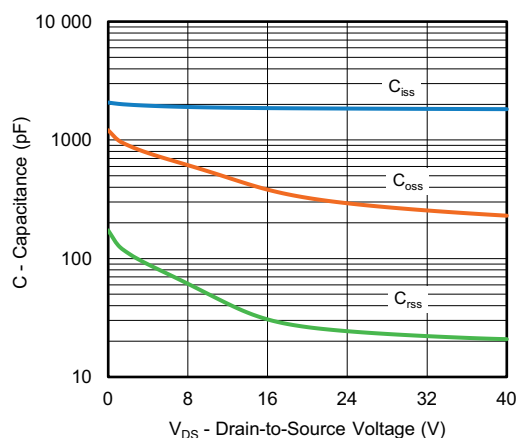
**Output Characteristics**



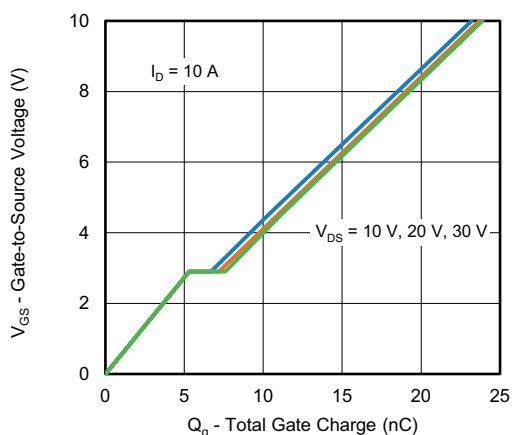
**Transfer Characteristics**



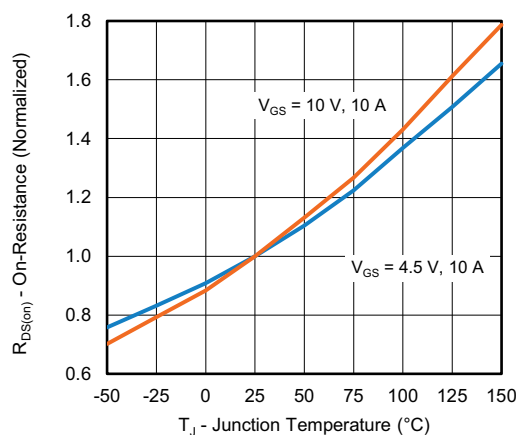
**On-Resistance vs. Drain Current**



**Capacitance**



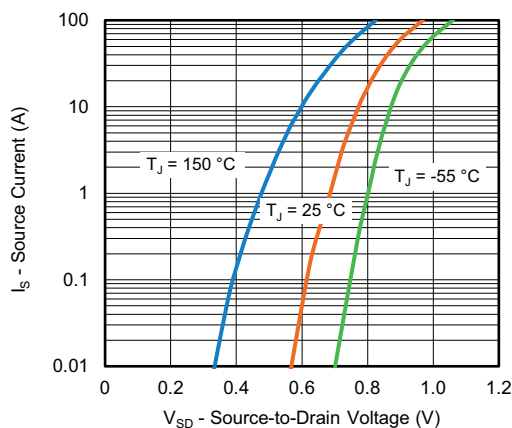
**Gate Charge**



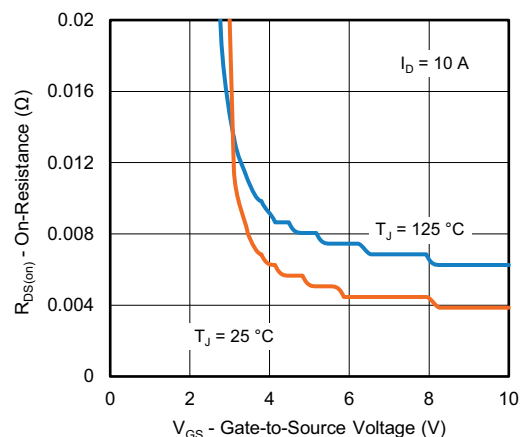
**On-Resistance vs. Junction Temperature**



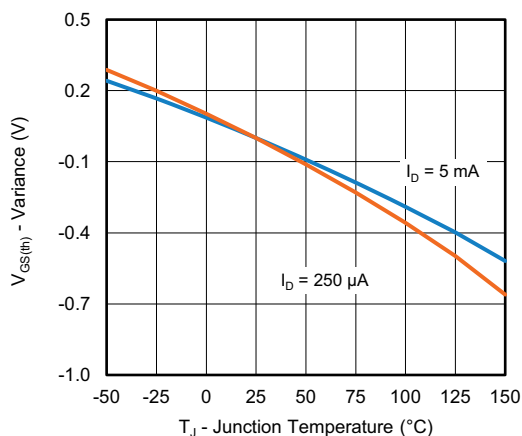
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



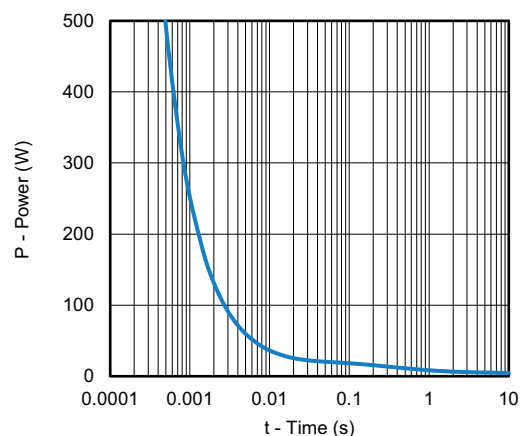
**Source-Drain Diode Forward Voltage**



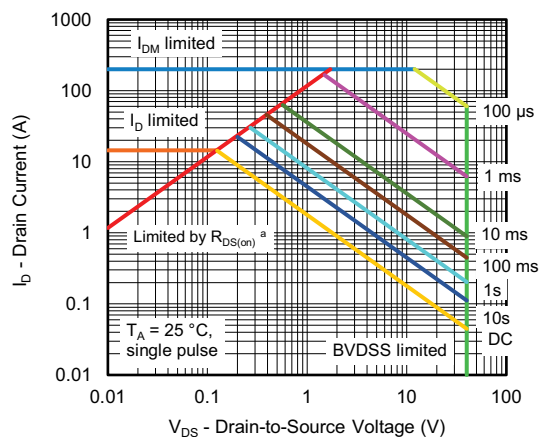
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



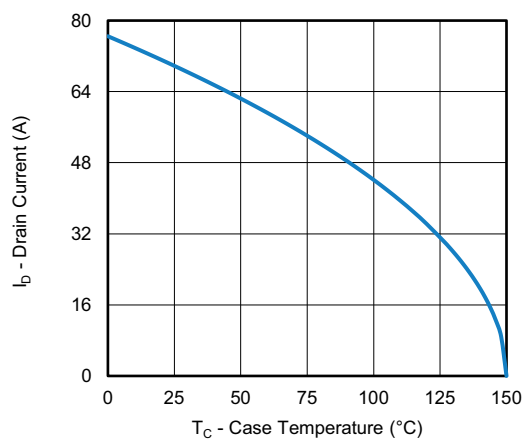
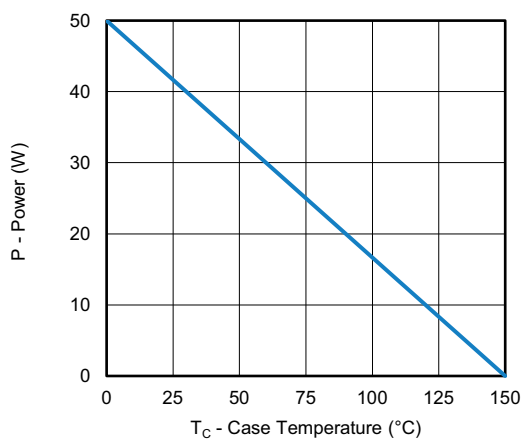
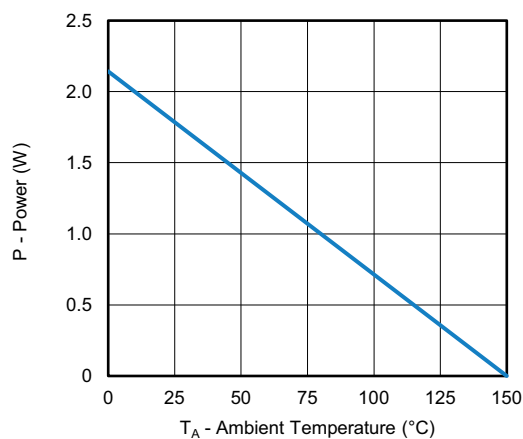
**Single Pulse Power, Junction-to-Ambient**



**Safe Operating Area**

**Note**

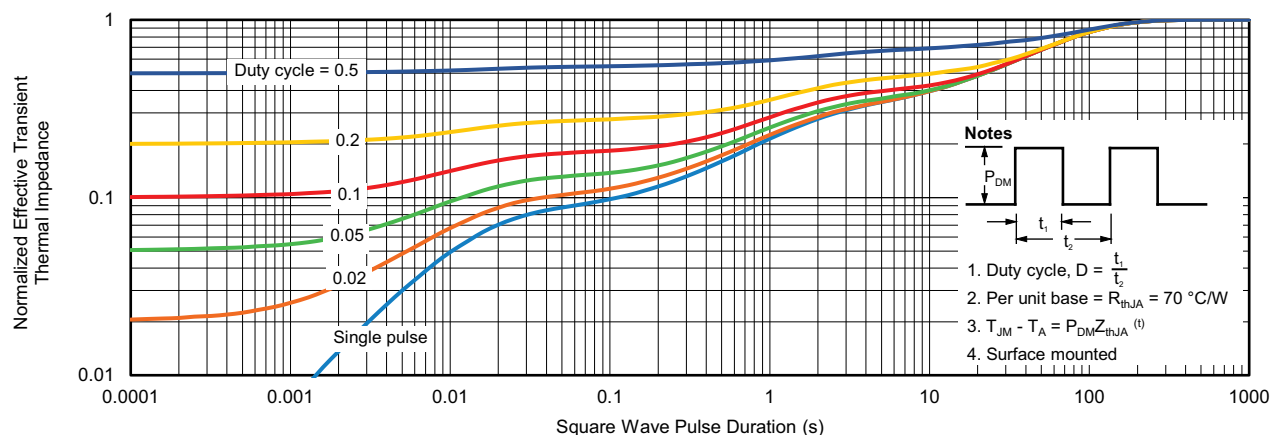
a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Current Derating <sup>a</sup>**

**Power, Junction-to-Case**

**Power, Junction-to-Ambient**
**Note**

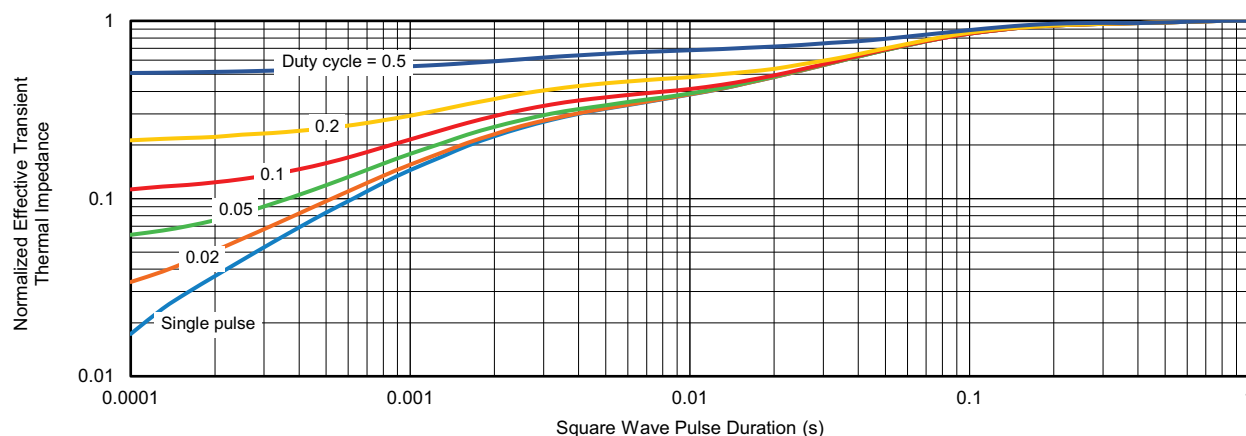
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**

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## PowerPAK® SO-8L Case Outline 1



Topside view



Backside view (single)



Backside view (dual)



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094			0.004		
b4	0.47			0.019		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3	2.96			0.117		
θ	0°	-	10°	0°	-	10°
ECN: S19-0643-Rev. E, 05-Aug-2019 DWG: 5976						

### Note

- Millimeters will govern





## RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads  
Dimensions in mm (inches)



## Disclaimer

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